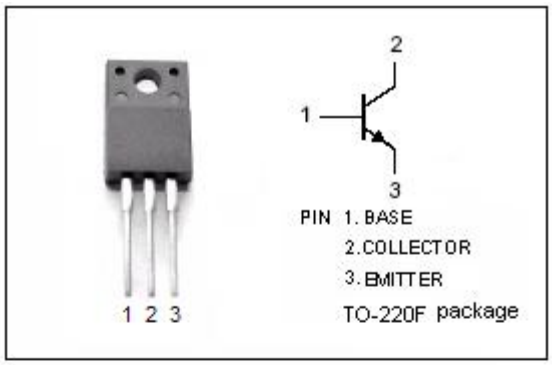
isc Silicon NPN Power Transistor 2SC4369



DESCRIPTION

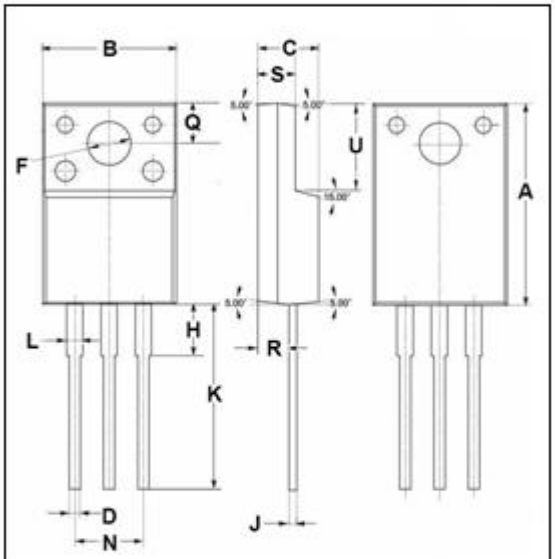
- Collector-Emitter Breakdown Voltage
  : V_{CEO}= 30V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SA1658
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current-Continuous	0.3	A
P_C	Collector Power Dissipation @T_C= 25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	30			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.2A			0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.5A; V_{CE}= 2V			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 20V; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	μA
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 2V	70		240	
h_{FE-2}	DC Current Gain	I_C= 2.5A; V_{CE}= 2V	25			
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1.0MHz		35		pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 2V		100		MHz